Ordering number : ENA0829

SANYO Semiconductors

DATA SHEET

N-Channel Silicon MOSFET

2SK4118LS — General-Purpose Switching Device Applications

Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- Adoption of high reliability HVP process.
- Attachment workability is good by Mica-less package.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		400	V
Gate-to-Source Voltage	V_{GSS}		±30	V
Drain Current (DC)	I_{Dc}*1	Limited only by maximum temperature	18	A
	I_{Dpack}*2	SANYO's ideal heat dissipation condition	11.9	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	60	A
Allowable Power Dissipation	P_D		2.0	W
		Tc=25°C (SANYO's ideal heat dissipation condition)	37	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C
Avalanche Energy (Single Pulse) *3	E_{AS}		427	mJ
Avalanche Current *4	I_{AV}		18	A

*1 Shows chip capability

*2 Package limited

*3 V_{DD}=99V, L=2mH, I_{AV}=18A

*4 L≤2mH, single pulse

Marking : K4118

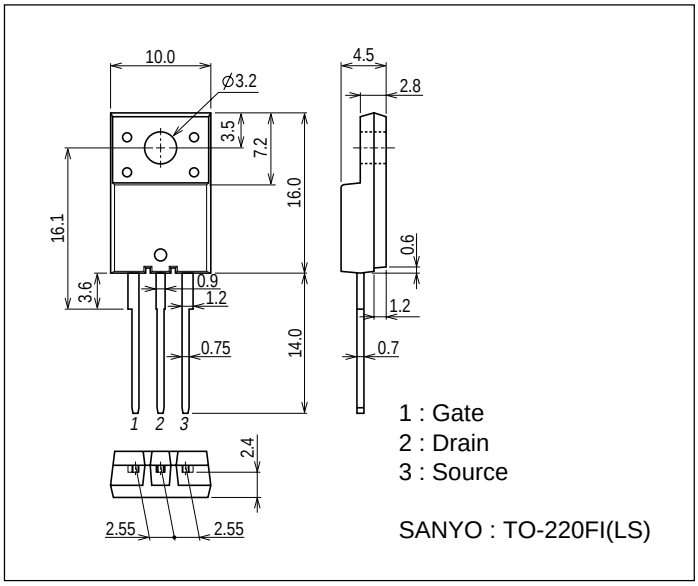
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=10mA, V_{GS}=0V	400			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=320V, V_{GS}=0V			100	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V			±100	nA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	3		5	V
Forward Transfer Admittance	|yfs|	V_{DS}=10V, I_D=9A	4	8		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)	I_D=9A, V_{GS}=10V		0.26	0.34	Ω
Input Capacitance	Ciss	V_{DS}=30V, f=1MHz		1000		pF
Output Capacitance	Coss	V_{DS}=30V, f=1MHz		240		pF
Reverse Transfer Capacitance	Crss	V_{DS}=30V, f=1MHz		52		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		25		ns
Rise Time	t_r	See specified Test Circuit.		100		ns
Turn-OFF Delay Time	t_d(off)	See specified Test Circuit.		108		ns
Fall Time	t_f	See specified Test Circuit.		49		ns
Total Gate Charge	Qg	V_{DS}=200V, V_{GS}=10V, I_D=18A		38.8		nC
Gate-to-Source Charge	Qgs	V_{DS}=200V, V_{GS}=10V, I_D=18A		6.7		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=200V, V_{GS}=10V, I_D=18A		25		nC
Diode Forward Voltage	V_{SD}	I_S=18A, V_{GS}=0V		0.9	1.2	V

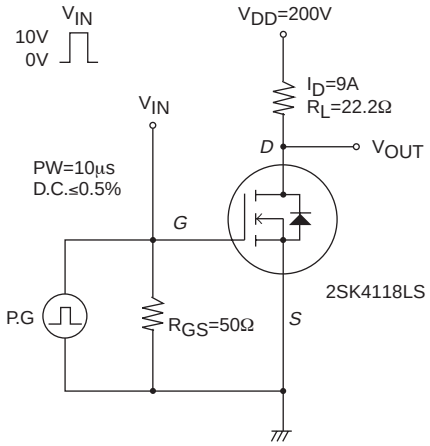
Package Dimensions

unit : mm (typ)

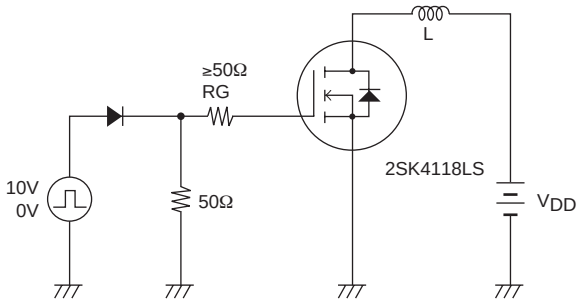
7509-002

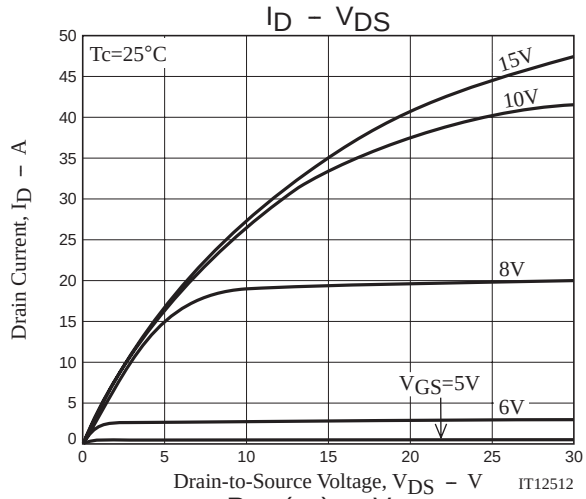


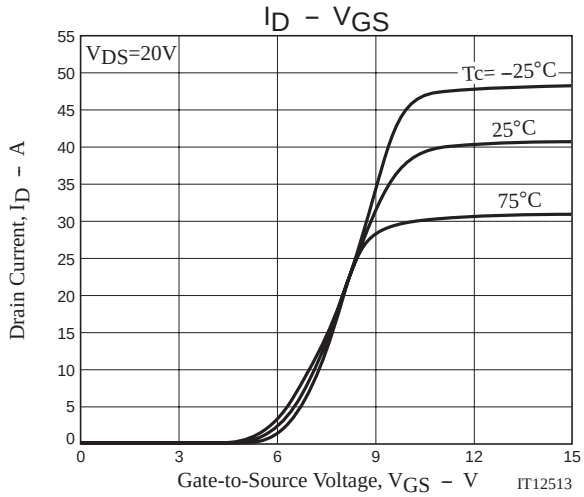
Switching Time Test Circuit

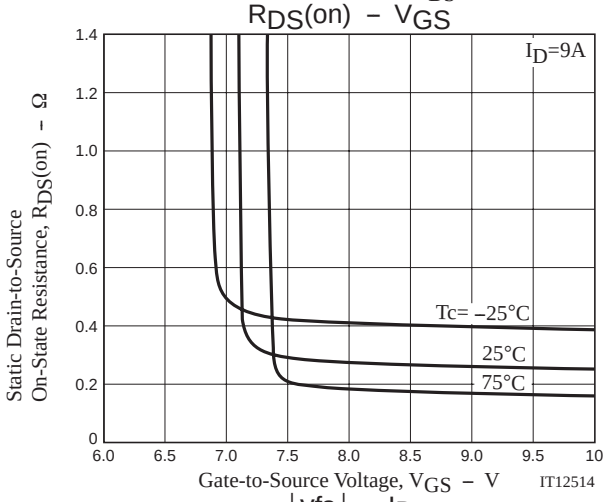


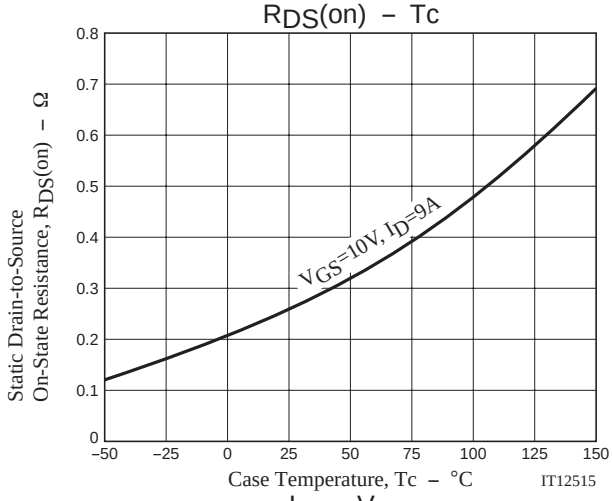
Avalanche Resistance Test Circuit

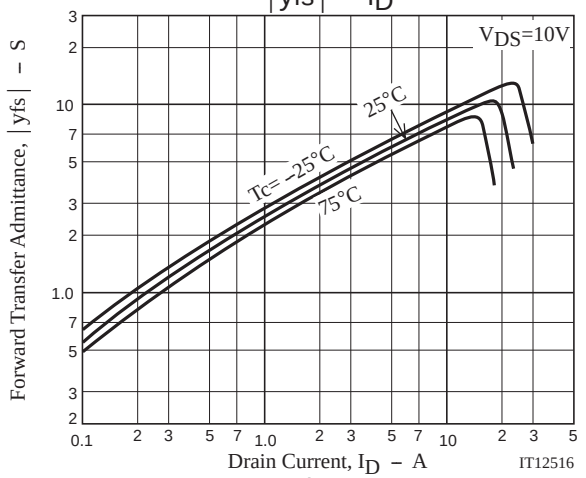


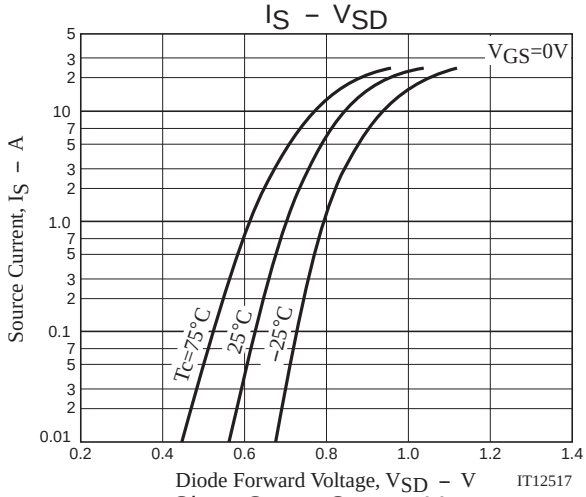

ID – VDS
Tc=25°C
15V
10V
8V
VGS=5V
6V
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT12512

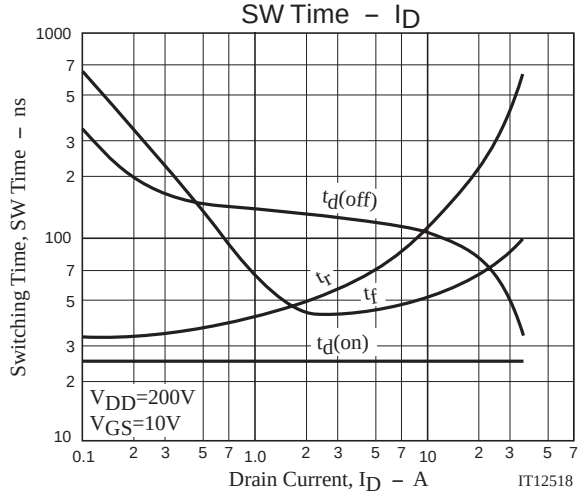

ID – VGS
VDS=20V
Tc= –25°C
25°C
75°C
Drain Current, ID – A
Gate-to-Source Voltage, VGS – V
IT12513

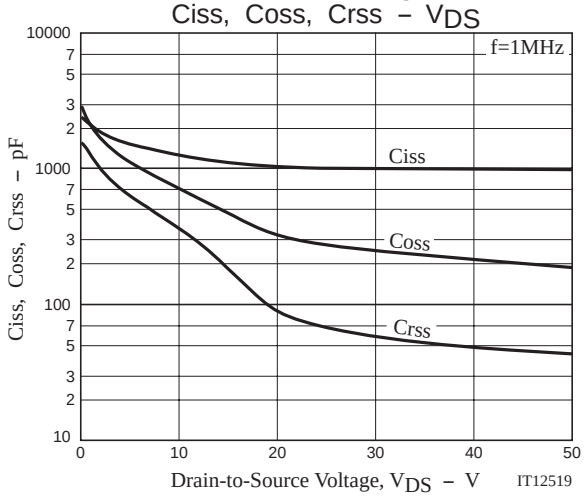

RDS(on) – VGS
ID=9A
Tc= –25°C
25°C
75°C
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Gate-to-Source Voltage, VGS – V
IT12514

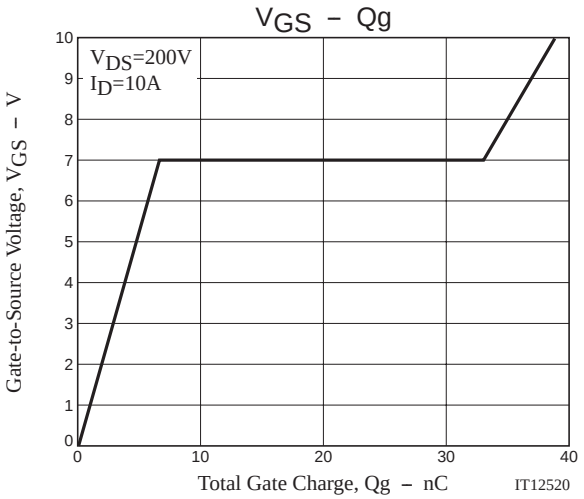

RDS(on) – Tc
VGS=10V, ID=9A
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Case Temperature, Tc – °C
IT12515

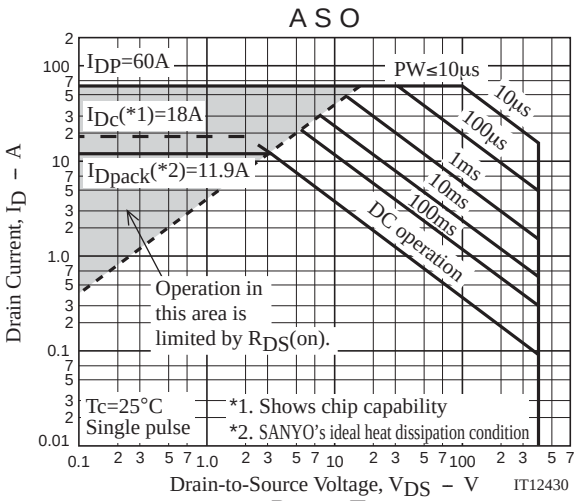

|yfs| – ID
VDS=10V
25°C
Tc= –25°C
75°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT12516

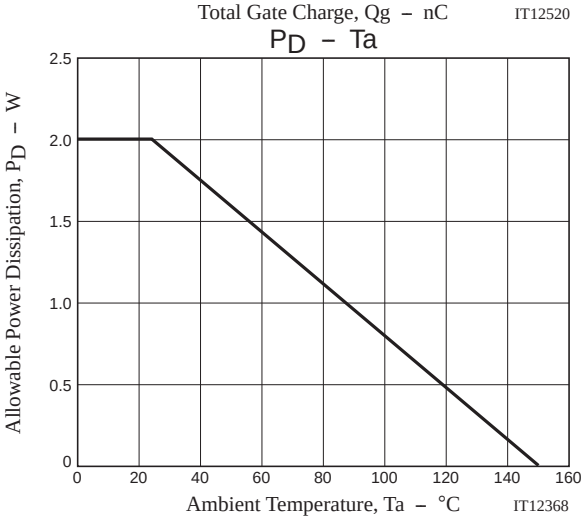

IS – VSD
VGS=0V
Tc=75°C
25°C
–25°C
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT12517

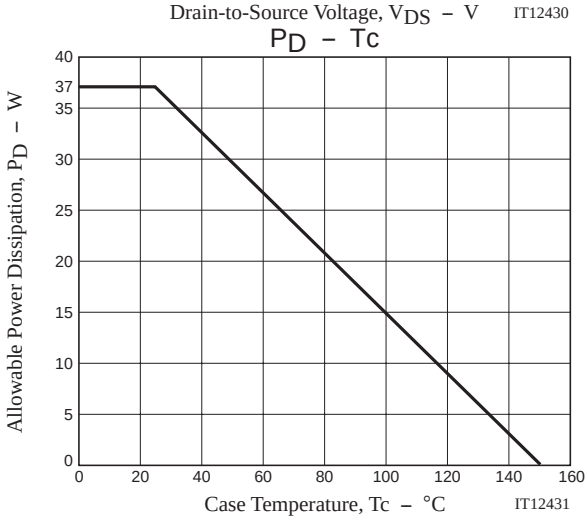

SW Time – ID
td(off)
tr
tf
td(on)
VDD=200V
VGS=10V
Switching Time, SW Time – ns
Drain Current, ID – A
IT12518

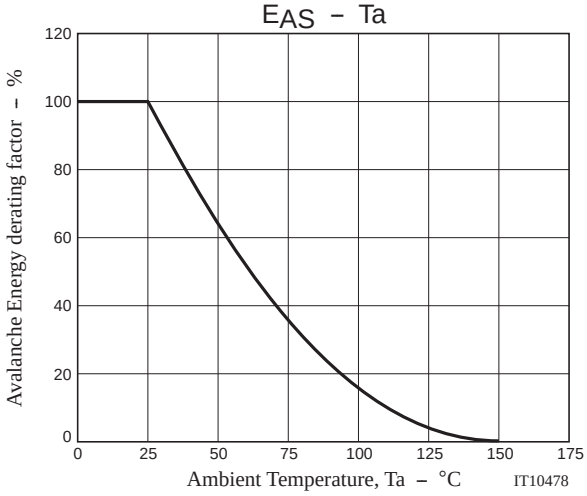

Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT12519


VGS – Qg
VDS=200V
ID=10A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT12520


A S O
IDP=60A
PW≤10μs
IDC(*1)=18A
IDpack(*2)=11.9A
10μs
100μs
1ms
10ms
100ms
DC operation
Operation in this area is limited by RDS(on).
Tc=25°C
Single pulse
*1. Shows chip capability
*2. SANYO's ideal heat dissipation condition
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT12430


PD – Ta
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT12368


PD – Tc
Allowable Power Dissipation, PD – W
Case Temperature, Tc – °C
IT12431


EAS – Ta
Avalanche Energy derating factor – %
Ambient Temperature, Ta – °C
IT10478

Note on usage : Since the 2SK4118LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

This catalog provides information as of June, 2007. Specifications and information herein are subject to change without notice.